

Barrierless Cu–Ni–Nb thin films on silicon with high thermal stability and low electrical resistivity– ERRATUM

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In Li et al., the affiliation *Key Laboratory of Materials Modification by Laser School of Mechanical Engineering, Dalian University of Technology, Ministry of Education, Dalian 116024, China* for Xiao Na Li, Li Rong Zhao, Li Jun Liu, and Chuang Dong is incorrect. It should read: *Key Laboratory of Materials Modification by Laser, Ion and Electron Beams, Dalian University of Technology, Ministry of Education, Dalian 116024, China*

The publisher regrets the mistake.

REFERENCE

1. X.N. Li, L.R. Zhao, Z. Li, L.J. Liu, C.M. Bao, J.P. Chu, and C. Dong: Barrierless Cu–Ni–Nb thin films on silicon with high thermal stability and low electrical resistivity. *J. Mater. Res.* **28**(24), 3367–3373 (2013).